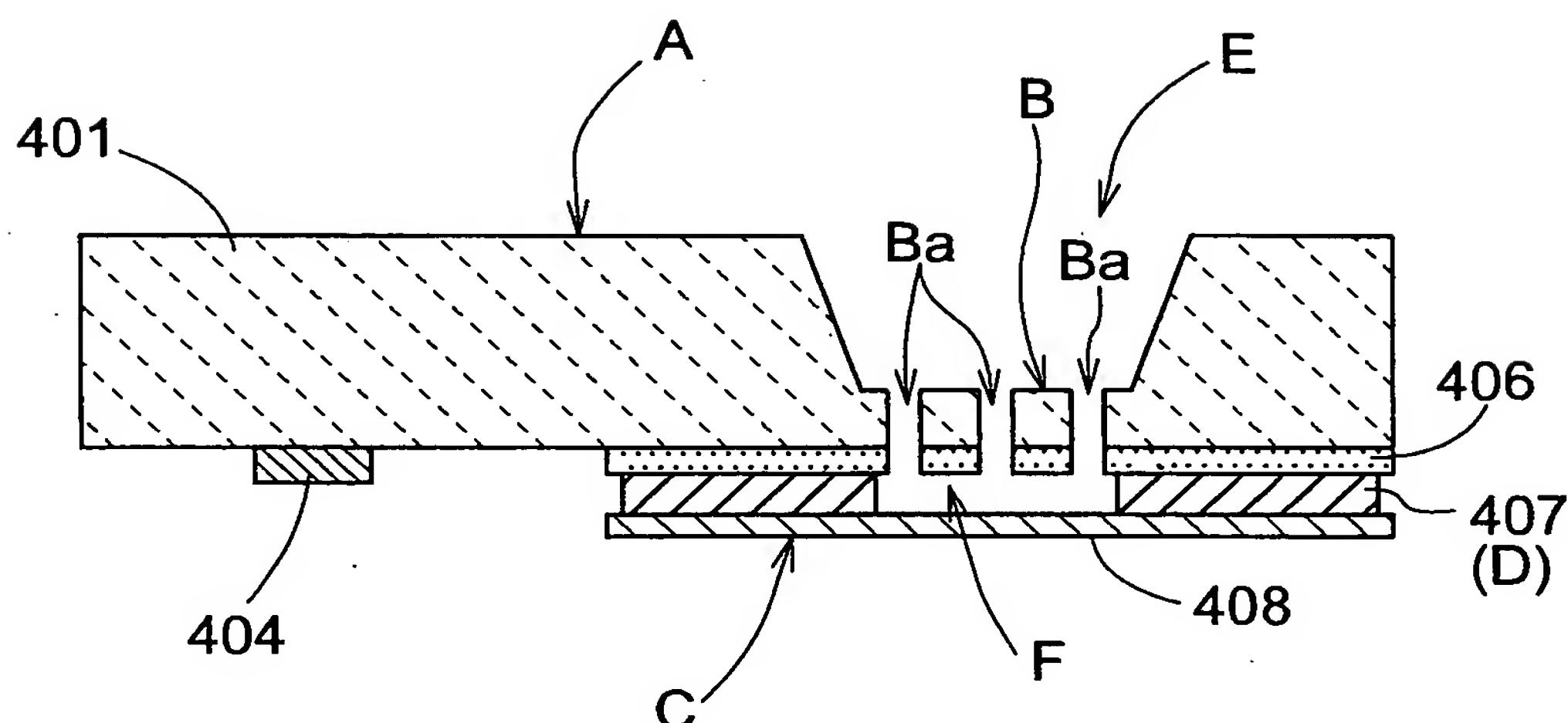


FIG. 1



A: substrate
B: back electrode
Ba: perforations
(acoustic holes)
C: diaphragm
D: spacer
E: acoustic opening
F: void area

401: silicon substrate
404: electrode portion
406: second protective film
407: sacrificial layer
408: metal film

FIG.2

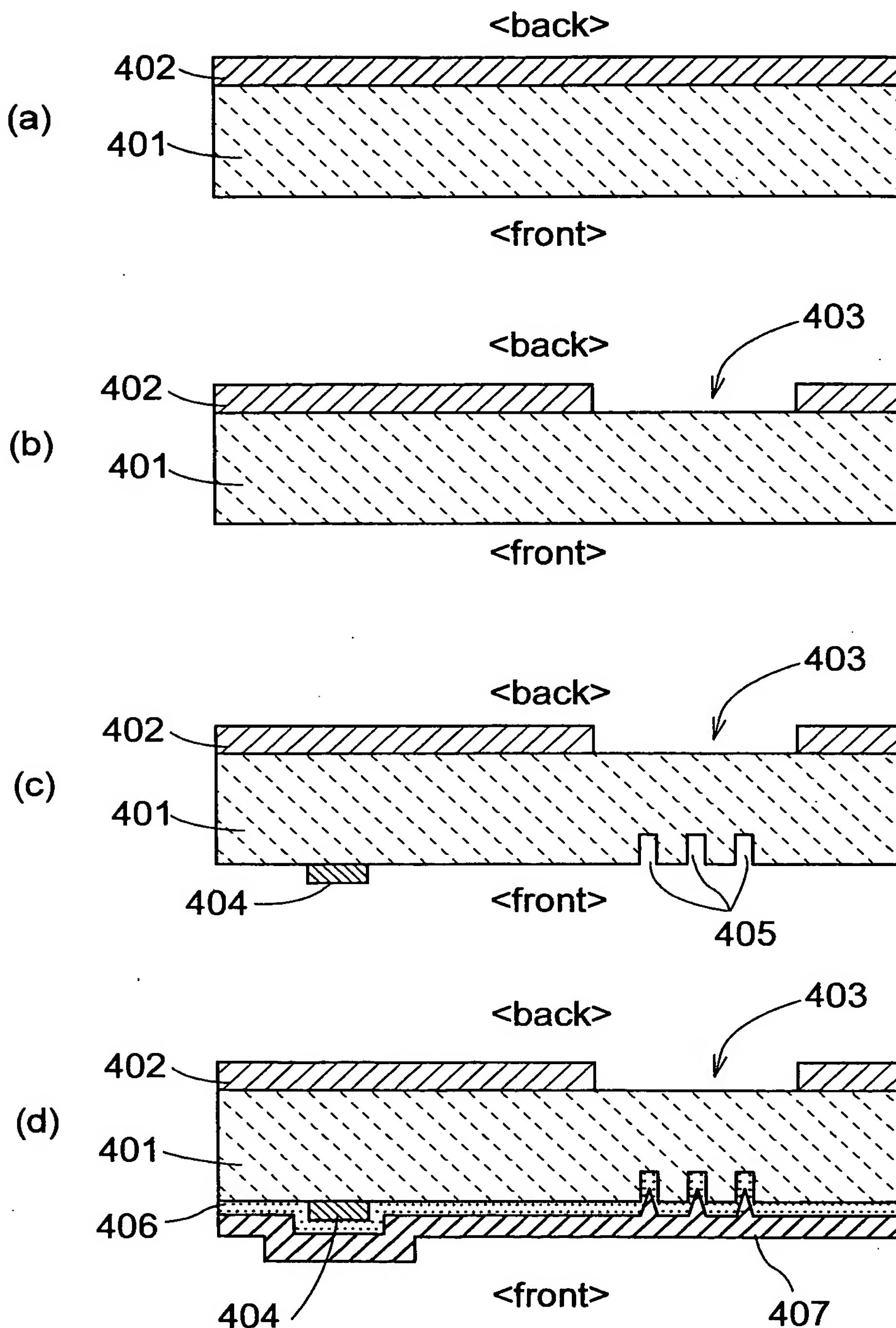


FIG.3

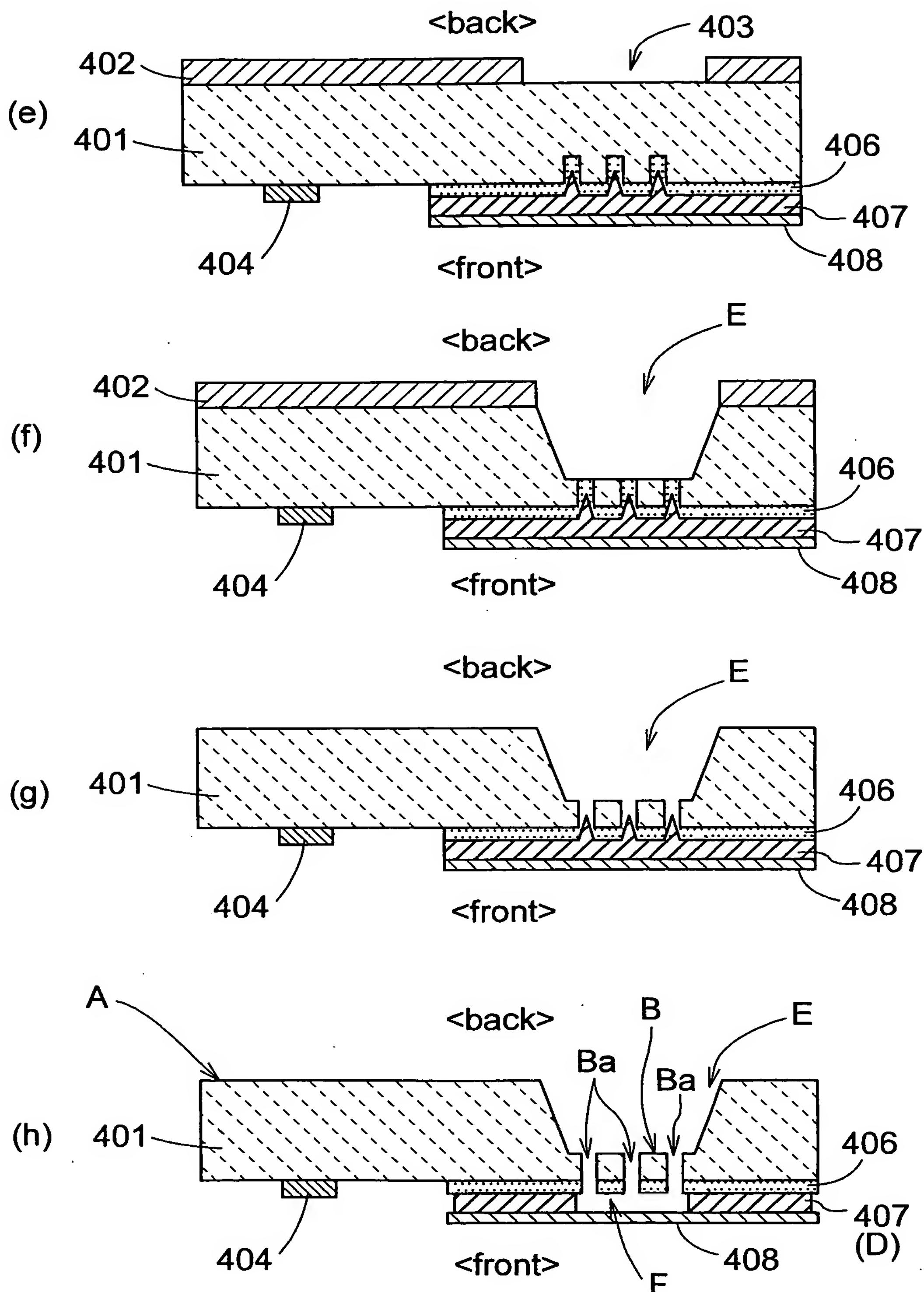


FIG.4

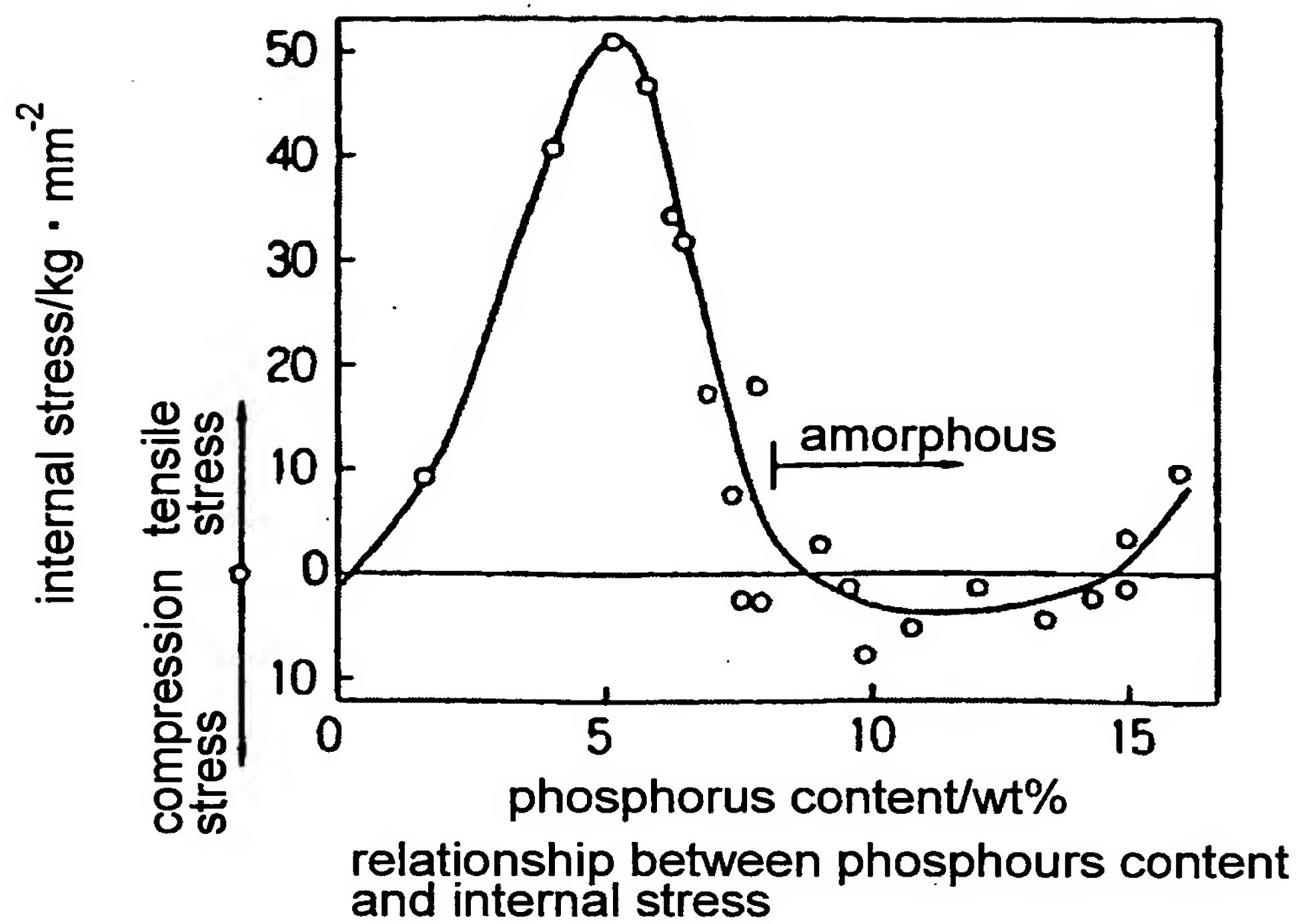
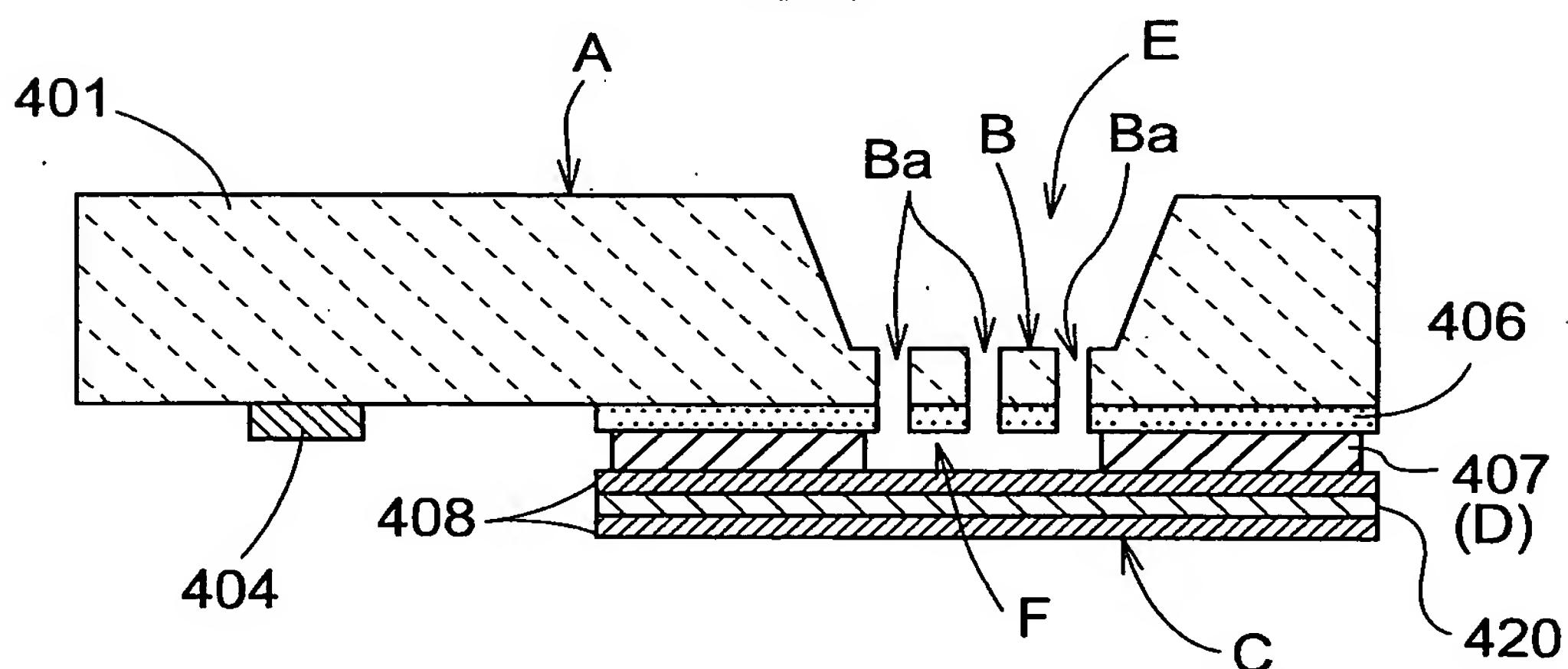


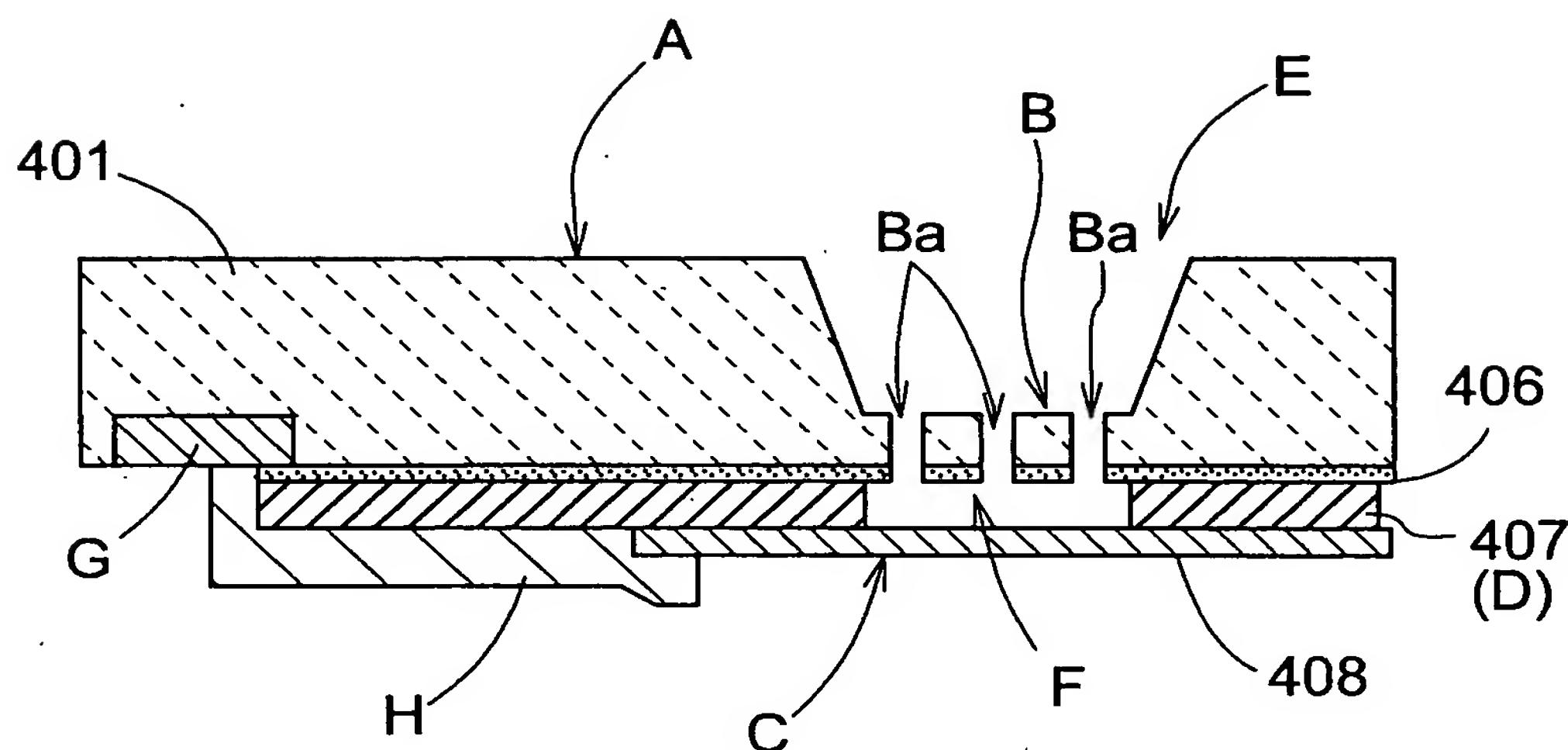
FIG.5



- A: substrate
- B: back electrode
- Ba: perforations (acoustic holes)
- C: diaphragm
- D: spacer
- E: acoustic opening
- F: void area

- 401: silicon substrate
- 404: electrode portion
- 406: second protective film
- 407: sacrificial layer
- 408: metal film
- 420: base layer

FIG.6



A: substrate
B: back electrode
Ba: perforations
(acoustic holes)
C: diaphragm
D: spacer
E: acoustic opening
F: void area
G: integrated circuit
H: wiring

401: silicon substrate
406: second protective film
407: sacrificial layer
408: metal film

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PRIOR ART

FIG. 7

